Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	1	702/35.ccls. and non near vibrat$4 with probe with potential	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/11/09 11:21
L2	1	702/36.ccls. and non near vibrat$4 with probe with potential	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/11/09 11:21
L3	1	438/12.ccls. and non near vibrat$4 with probe with potential	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/11/09 11:21
L4	1	134/1.3.ccls. and non near vibrat$4 with probe with potential	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/11/09 11:21
L5	6	(non near vibrat$4 with probe with potential).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/11/09 11:23
L6	9	(non near vibrat$4 with difference with potential).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/11/09 11:23
L7	7	(non near vibrat$4 with difference with potential and chemical).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/11/09 11:23
L8	2	(non near vibrat$4 with difference with potential and chemical and sample).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/11/09 11:23
S1	1	nvcpd near sensor	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/11/09 11:20
S2	1	nvcpd	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2004/09/07 11:15
S3	2	scan$4 same wafer same sensor same voltage same vibrat$4	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2004/09/07 11:16
S4	85	scan$4 same wafer same sensor same voltage	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2004/09/07 11:22

S5	57	vibrat$3 with contact with potential with difference	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2004/09/07 11:22
S6	21	vibrat$3 with contact with potential with difference and semiconductor	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2004/09/07 13:20
S7	5	non near vibrat$3 with contact with potential with difference	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2004/09/07 13:04
S8	6	non near vibrat$3 with potential with difference	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2004/09/07 13:05
S9	1	vibrat$3 with contact with potential with difference and semiconductor and defect and wafer	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2004/09/07 13:08
S10	2	vibrat$3 with contact with potential with difference and semiconductor and defect	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2004/09/07 13:09
S11	12	vibrat$3 with contact with potential with difference and wafer	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2004/09/19 11:07
S12	1	1991-213740.NRAN.	DERWENT	OR	OFF	2004/09/07 13:20
S13	7	defect same semiconductor and contact same potential same difference same sensor	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2004/09/13 12:42
S14	7	defect same semiconductor and contact same potential same difference same vibrat$3	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2004/09/13 12:45
S15	0	defect same semiconductor and Kelvin same (non near vibrat$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2004/09/13 12:46
S16	11	defect same semiconductor and Kelvin same vibrat$3	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2004/09/13 12:46
S17	4	category with defect with chemical	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2004/09/19 10:59

S18	9	category with defect with electronic	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2004/09/19 10:53
S19	71	treat with defect with improv$3	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2004/09/19 11:00
S20	6	treat with defect with improv$3 and semiconductor	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2004/09/19 11:01
S21	99	treat$3 with defect with improv$3 and semiconductor	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2004/09/19 11:02
S22	329	treat$5 with defect with improv$3 and semiconductor	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2004/09/19 11:02
S23	6	(analyz$3 analysis) with chemical with contaminant with auger	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2004/09/19 11:08
S24	119	take.inv. and semiconductor	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2004/09/23 12:23
S25	1	wafer near handler and remed$4 with defect and clean$3 and semiconductor	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2004/09/23 12:30
S26	1	wafer near handler and remed$4 with defect and semiconductor	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2004/09/23 12:30
S27	39	wafer near handler and clean$3 with defect and semiconductor	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2004/09/23 12:32
S28	25	wafer near handler and clean$3 with defect and semiconductor and sensors!	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2004/09/23 12:35
S29	27	wafer near handler and clean$3 same defect and semiconductor and sensors!	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2004/09/23 14:41

S30	518	sensors! same clean$3 same (semiconductor wafer)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2004/09/23 14:42
S31	36	sensors! same clean$3 same (semiconductor wafer) same handl$3	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2004/09/23 14:43
S32	13	438/906.ccls. and sensors!	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2004/09/23 15:11
S33	26	438/906.ccls. and sensors	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2004/09/23 15:12
S34	9	438/12.ccls. and sensors	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2004/09/23 15:12
S35	6	438/12.ccls. and sensors!	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2004/09/23 15:14
S36	18	438/12.ccls. and clean$3	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2004/09/23 15:20
S37	6	438/12.ccls. and sensors!	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2004/09/23 15:21
S38	3	sensors! same clean$3 same semiconductor same defect	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2004/09/23 15:23
S39	14	sensors same clean$3 same semiconductor same defect	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2004/09/23 16:03
S40	0	sensors same remed$4 same semiconductor same defect	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2004/09/23 16:02
S41	96	sensors same clean$3 same semiconductor and defect	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2004/09/23 16:03

S42	3	sensors same clean$3 same semiconductor same monitor$3 and defect	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2004/09/23 16:05
S43	64	134/1.3.ccls. and sensors!	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2004/09/23 16:16
S44	24	134/1.2.ccls. and sensors!	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2004/09/23 16:16
S45	269	transport$3 same clean same (semiconductor wafer) same handl$3	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2004/09/24 12:34
S46	0	transport$3 same clean same (semiconductor wafer) same handl$3 same defect	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2004/09/24 12:34
S47	71	transport$3 same clean same (semiconductor wafer) same handl$3 and defect	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2004/09/24 12:36
S48	0	transport$3 same clean$4 same (semiconductor wafer) same handl$3 same defect	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2004/09/24 12:37
S49	111	transport$3 same clean$4 same (semiconductor wafer) same handl$3 and defect	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2004/09/24 12:50
S50	46	transport$3 same defect same (semiconductor wafer) same handl$3	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2004/09/24 13:02
S51	31	monitor$3 with clean$3 same (semiconductor wafer) same sensors!	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2004/09/24 13:17
S52	7	determin$3 same cleanliness same wafer same improv$3	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2004/09/24 13:20
S53	7	determin$3 same cleanliness same semiconductor same improv$3	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2004/09/24 13:21

S54	594	modify$3 same clean$3 same improv$	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2004/09/24 13:21
S55	36	modify$3 same clean$3 same improv$ same (wafer semiconductor)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2004/09/24 13:22
S56	28	decompos$3 with signal with wavelet with domain	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/09/12 13:43
S57	6	decompos$3 with signal with wavelet with domain and coefficient and peak	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/09/12 13:52
S58	118	signal with wavelet with domain and coefficient and peak	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/09/12 13:52
S59	87	signal with wavelet with domain and coefficient and peak and $2compos$3	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/09/12 14:42
S60	6	$2compos$3 with signal with wavelet with domain and coefficient and peak	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/09/12 13:52
S61	32	signal with wavelet with domain and coefficient and peak and $2compos$3 and revers$3	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/09/12 13:53
S62	13	signal with wavelet with domain and coefficient and peak and revers$3 near order	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/09/12 13:57
S63	30	signal with wavelet with domain and coefficient and peak and revers$3 and $2compress$3	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/09/12 14:48
S64	8	signal with wavelet with domain and coefficient and peak and revers$3 same coefficient and $2compress$3	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/09/12 14:11
S65	0	model with circuit with RC and convert$3 with discrete with time and impulse near response and deconvolut$3	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/09/12 14:13

S66	1	model with circuit and convert$3 with discrete with time and impulse near response and deconvolut$3	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/09/12 14:21
S67	4	model$3 with circuit and convert$3 with discrete with time and impulse near response and deconvolut$3	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/09/12 14:23
S68	14	non near vibrat$4 with contact with potential with difference with sensor	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/09/12 14:26
S69	8	non near vibrat$4 with contact with potential with difference with sensor and defect$3	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/09/12 14:26
S70	5	signal with wavelet with domain and coefficient and peak and backward and $2compress$3	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/09/12 14:50
S71	28	signal with wavelet with domain and coefficient and peak and (transpos$3 invert$3) and $2compress$3	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/09/12 15:01
S72	0	signal with wavelet with domain and coefficient and peak and (transpos$3 invert$3) same coefficient and $2compress$3	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/09/12 14:50
S73	8	signal with wavelet with domain and coefficient and peak and (revers$3) same coefficient and $2compress$3	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/09/12 15:02
S74	4	"631469".ap.	US-PGPUB; USPAT	OR	OFF	2005/09/27 15:40
S75	16	non near vibrat$4 with potential with difference with sensor	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/11/04 16:18
S76	3	non near vibrat$4 with potential with difference with sensor and chuck	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/11/03 13:44
S77	2	"6011404".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/11/04 16:18